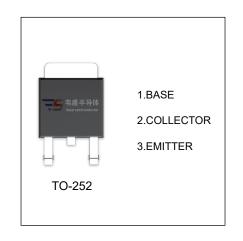


2SA1012 TRANSISTOR (PNP)

FEATURES

- High Current Switching Applications.
- Low Collector Saturation Voltage
- High Speed Swithing Time



MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	-60	V	
V _{CEO}	Collector-Emitter Voltage	-50	V	
V _{EBO}	Emitter-Base Voltage	-5 V		
Ic	Collector Current -Continuous	-5	Α	
Pc	Collector Power Dissipation	1.25	W	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	100	°C/W	
T _j	Junction Temperature	150	℃	
T _{stg}	Storage Temperature Range	-55~+150	℃	

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-0.1mA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =-10mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-1	μΑ
	h _{FE(1)}	V _{CE} =-1V, I _C =-1A	70		240	
DC current gain	h _{FE(2)} *	V _{CE} =-1V, I _C =-3A	30			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-3A, I _B =-150mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =-3A, I _B =-150mA			-1.2	V
Transition frequency	f _T	V _{CE} =-4V, I _C =-1A		60		MHz
Collector output capacitance	Cob	V _{CB} =-10V, I _E =0, f=1MHz		170		pF
Turn-on Time	t _{on}	\/ - 20\/ I - 2A		0.1		
Storage Time	t _s	V_{CC} =-30V, I_{C} =-3A, I_{B1} =- I_{B2} =-0.15A		1.0		μs
Fall Time	t _f	181-182-0.137		0.1		

^{*}Pulse test: t_p≤300μs, **δ**≤0.02.

CLASSIFICATION of $h_{\text{FE}((1)}$

Rank	0	Υ
Range	70-140	120-240



